

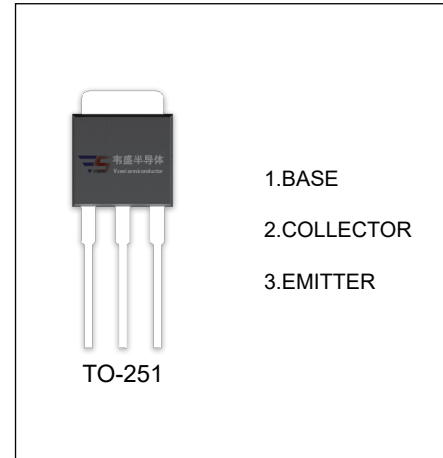
2SD1899-Z TRANSISTOR (NPN)

FEATURES

- High h_{FE}
- Low $V_{CE(sat)}$

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	1	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=200\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=600\text{mA}$	100		400	
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5\text{A}, I_B=150\text{mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1.5\text{A}, I_B=150\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=1.5\text{A}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		30		pF
Switching Time	Turn on Time	t_{on}			0.5	μs
	Storage Time	t_{stg}	$V_{CC}=10\text{V}, I_C=1\text{A}, I_{B1}=-I_{B2}=-0.1\text{A}$		2.0	
	Fall Time	t_f			0.5	

CLASSIFICATION OF $h_{FE(2)}$

Rank	M	L	K
Range	100-200	160-320	200-400

